ISP817-32

HIGH DENSITY MOUNTING PHOTOTRANSISTOR OPTICALLY COUPLED ISOLATORS

APPROVALS

- UL recognised, File No. E91231
  Package Code EE

'X' SPECIFICATION APPROVALS

- VDE 0884 in 3 available lead form : -
  - STD
  - G form
  - SMD approved to CECC 00802
- Certified to EN60950 by :-

  Nemko - Certificate No. P96102022

DESCRIPTION

The ISP817-32 optically coupled isolator consists of an infrared light emitting diode and NPN silicon photo transistor in space efficient dual in line plastic package.

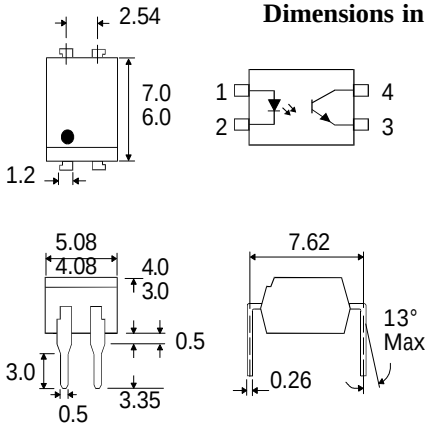
FEATURES

- Options :-
  10mm lead spread - add G after part no.
  Surface mount - add SM after part no.
  Tape&reel - add SMT&R after part no.
- Specially Selected Current Transfer Ratio
- High Isolation Voltage ($5.3kV_{RMS}$, $7.5kV_{PK}$)
- High BV_{CEO} (35Vmin)
- All electrical parameters 100% tested
- Custom electrical selections available

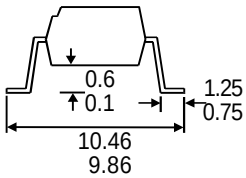
APPLICATIONS

- Computer terminals
- Industrial systems controllers
- Measuring instruments
- Signal transmission between systems of different potentials and impedances

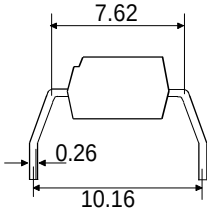
Dimensions in mm



OPTION SM
SURFACE MOUNT



OPTION G



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ABSOLUTE MAXIMUM RATINGS
(25°C unless otherwise specified)

Storage Temperature	-55°C to + 125°C
Operating Temperature	-55°C to + 100°C
Lead Soldering Temperature (1/16 inch (1.6mm) from case for 10 secs)	260°C

INPUT DIODE

Forward Current	50mA
Reverse Voltage	6V
Power Dissipation	70mW

OUTPUT TRANSISTOR

Collector-emitter Voltage BV_{CEO}	35V
Emitter-collector Voltage BV_{ECO}	6V
Power Dissipation	150mW

POWER DISSIPATION

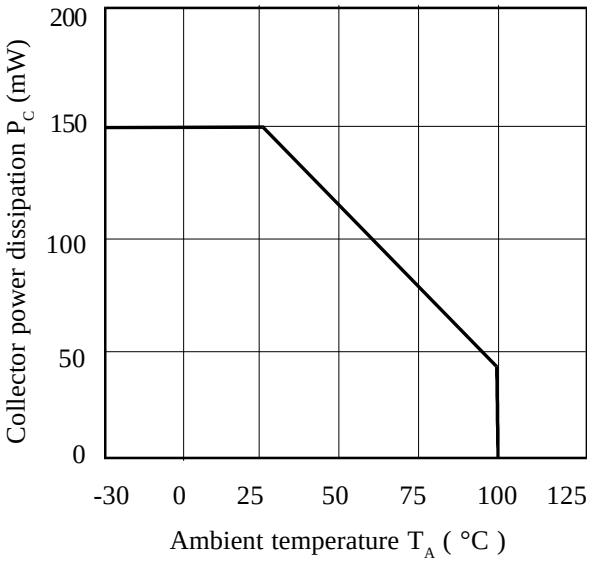
Total Power Dissipation	200mW
(derate linearly 2.67mW/°C above 25°C)	

ELECTRICAL CHARACTERISTICS (T_A = 25°C Unless otherwise noted)

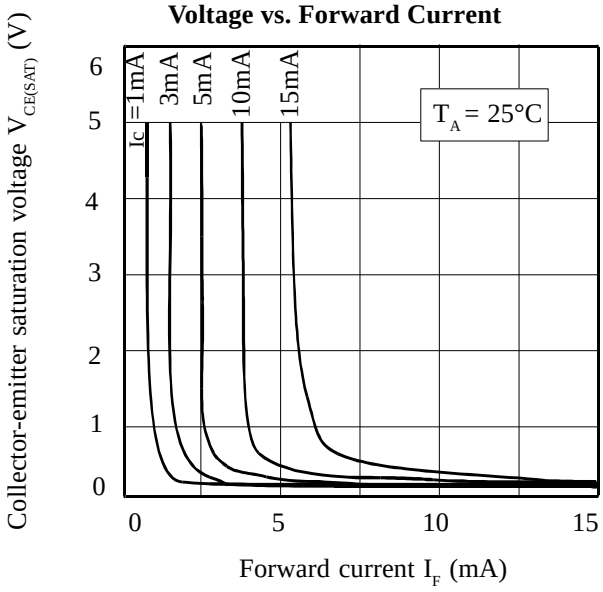
PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage (V_F)		1.2	1.4	V	I_F = 20mA
	Reverse Voltage (V_R)	6			V	I_R = 10µA
	Reverse Current (I_R)			10	µA	V_R = 6V
Output	Collector-emitter Breakdown (BV_{CEO})	35			V	I_C = 1mA
	Emitter-collector Breakdown (BV_{ECO})	6			V	I_E = 100µA
	Collector-emitter Dark Current (I_{CEO})			100	nA	V_{CE} = 20V
Coupled	Current Transfer Ratio (CTR) (Note 2)					
		75			%	1mA I_F, 5V V_{CE}
		35			%	0.4mA I_F, 5V V_{CE}
	Collector-emitter Saturation Voltage $V_{CE(SAT)}$			0.2	V	20mA I_F, 1mA I_C
	Input to Output Isolation Voltage V_{ISO}	5300			V_{RMS}	See note 1
		7500			V_{PK}	See note 1
	Input-output Isolation Resistance R_{ISO}	$5x10^{10}$			Ω	V_{IO} = 500V (note 1)
	Output Rise Time tr		4	18	µs	V_{CE} = 2V ,
	Output Fall Time tf		3	18	µs	I_C = 2mA, R_L = 100Ω

Note 1 Measured with input leads shorted together and output leads shorted together.
Note 2 Special Selections are available on request. Please consult the factory.

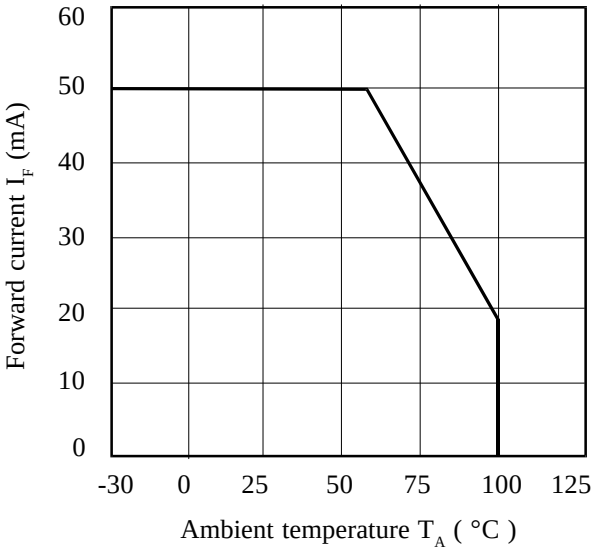
Collector Power Dissipation vs. Ambient Temperature



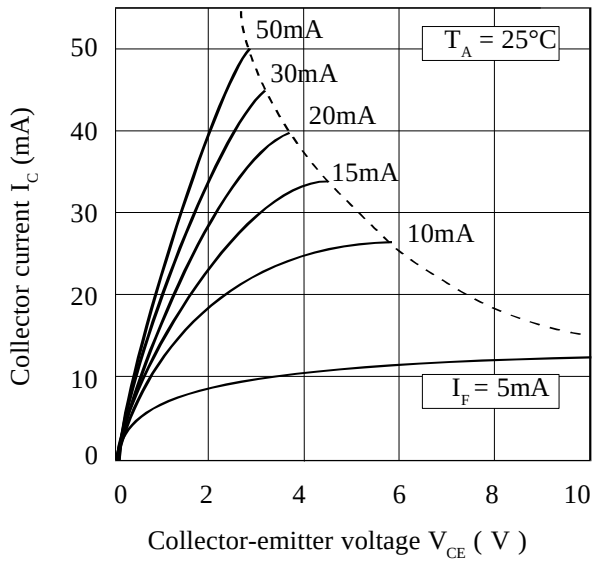
Collector-emitter Saturation Voltage vs. Forward Current



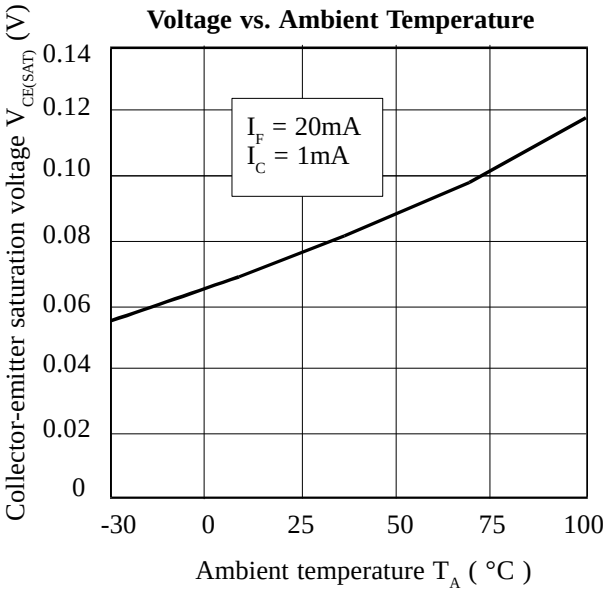
Forward Current vs. Ambient Temperature



Collector Current vs. Collector-emitter Voltage



Collector-emitter Saturation Voltage vs. Ambient Temperature



Current Transfer Ratio vs. Forward Current